Description

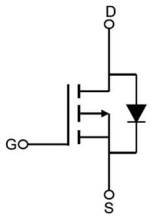
Features

- V_{DS}=-12V, I_D=-4.1A
  $R_{DS(ON)}$ <36mΩ @ V_{GS} = -4.5V
  $R_{DS(ON)}$ <53mΩ @ V_{GS} = -2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

- PWM Applications
- Load Switch
- Power Management

SOT-23-3



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM2305B-S2	VSM2305B	TAPING	SOT-23-3	7inch	3000	180000

Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-12	V
V_{GSS}	Gate-Source Voltage		±8	V
I_D	Continuous Drain Current	T_C = 25℃	-4.1	A
		T_C = 100℃	-2.6	
I_{DM}	Pulsed Drain Current note1		-16	A
P_D	Power Dissipation	T_C = 25℃	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		125	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-12	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =-12V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.4	-0.65	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =-4.5V, I_D =-4.1A	-	26	36	mΩ
		V_{GS} =-2.5V, I_D =-3A	-	35	53	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -4V, V_{GS} = 0V, f = 1.0MHz	-	905	-	pF
C_{oss}	Output Capacitance		-	210	-	pF
C_{rss}	Reverse Transfer Capacitance		-	195	-	pF
Q_g	Total Gate Charge	V_{DS} = -4V, I_D = -4.1A, V_{GS} = -4.5V	-	7.8	15	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	1.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -4V, I_D = -3.3A, R_G=1.0Ω, V_{GEN}=-4.5V, R_L=1.2Ω	-	13	20	ns
t_r	Turn-on Rise Time		-	35	53	ns
$t_{d(off)}$	Turn-off Delay Time		-	32	48	ns
t_f	Turn-off Fall Time		-	10	20	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -4.1A	-	-	-1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} =0V, I_S=-4.1A, di/dt=100A/μs	-	20	-	ns
Q_{rr}	Reverse Recovery Charge		-	9	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Figure1: Output Characteristics

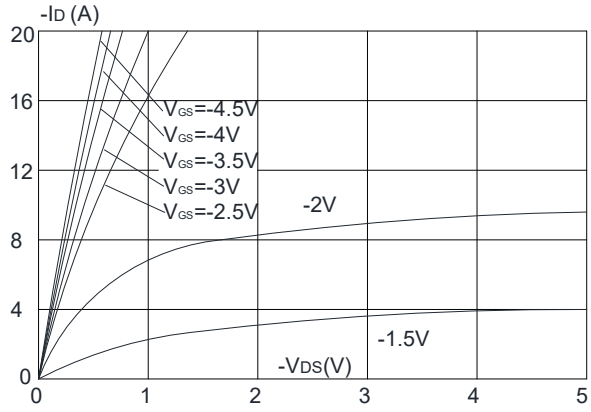


Figure 2: Typical Transfer Characteristics

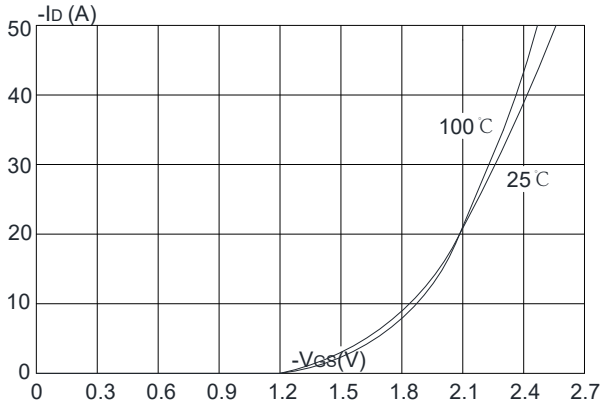


Figure 3: On-resistance vs. Drain Current

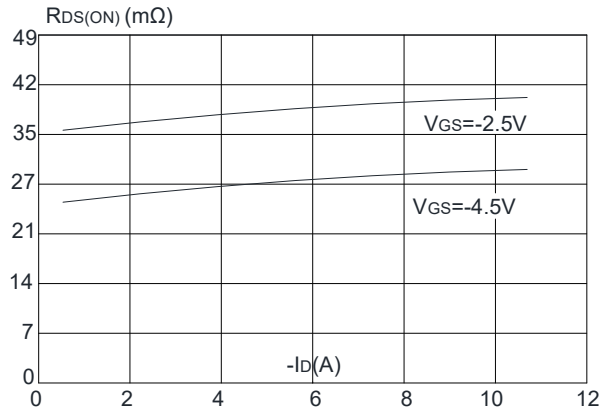


Figure 4: Body Diode Characteristics

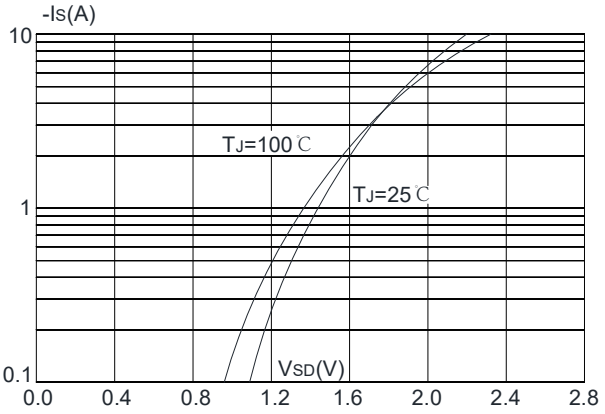


Figure 5: Gate Charge Characteristics

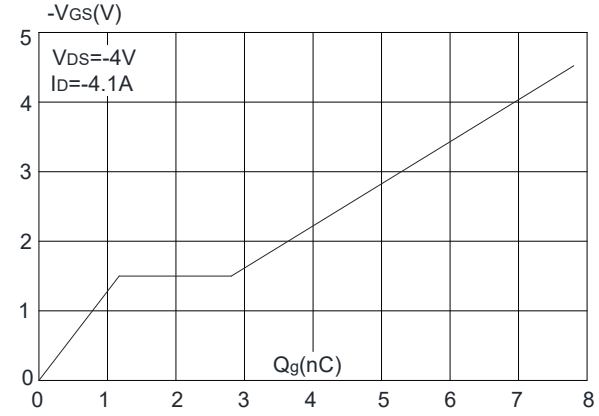


Figure 6: Capacitance Characteristics

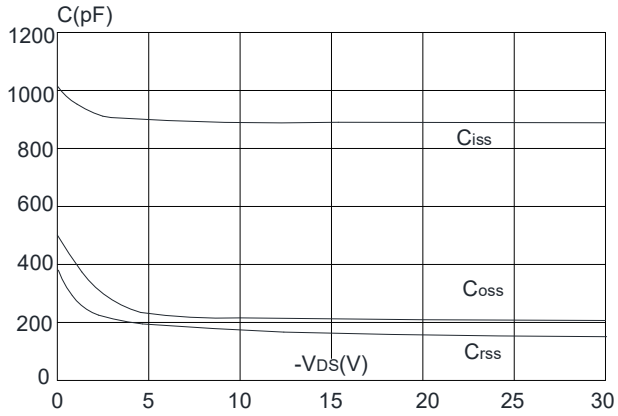


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

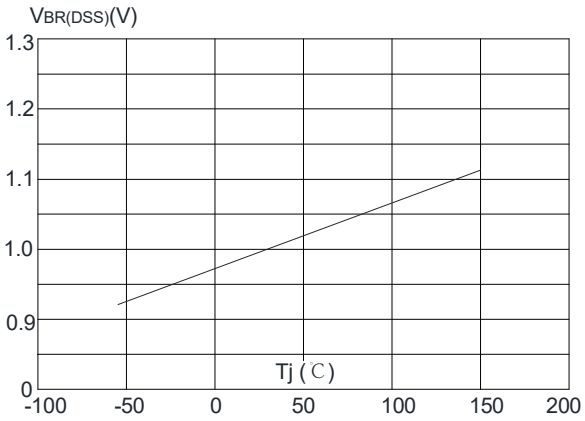


Figure 8: Normalized on Resistance vs. Junction Temperature

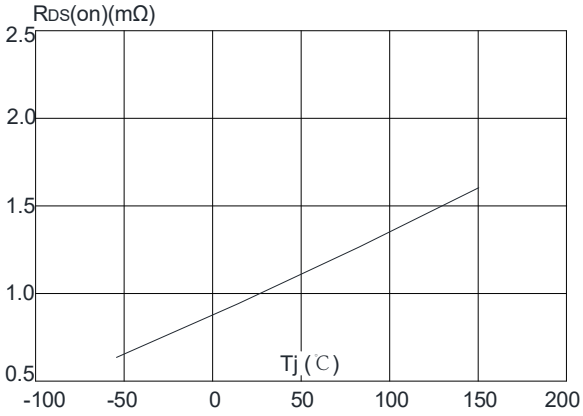


Figure 9: Maximum Safe Operating Area

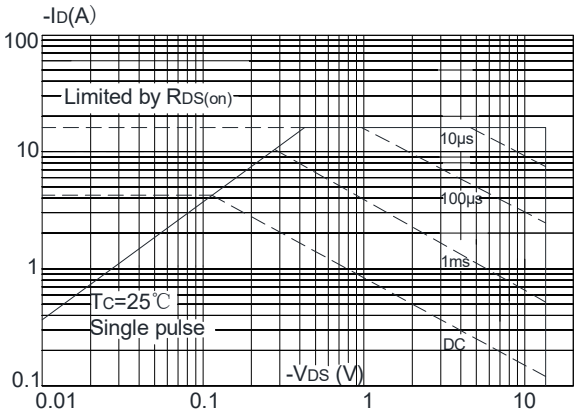


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

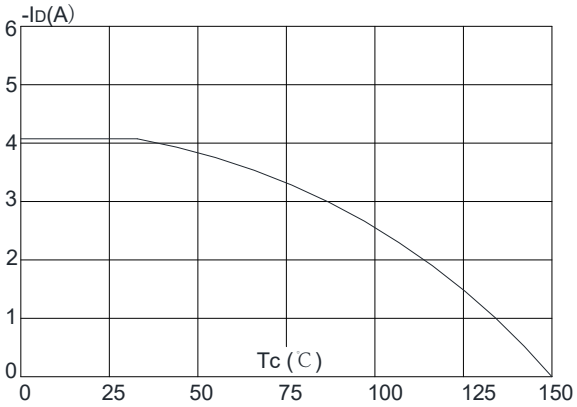
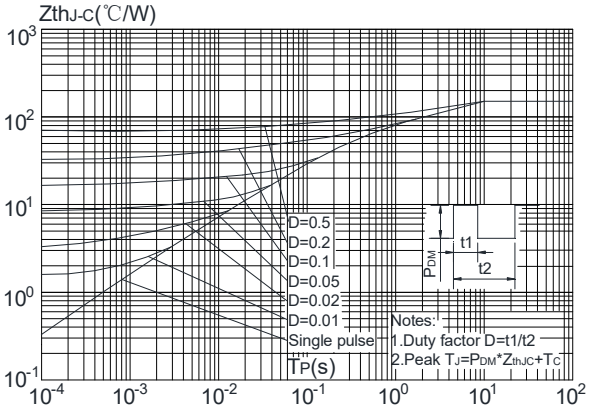
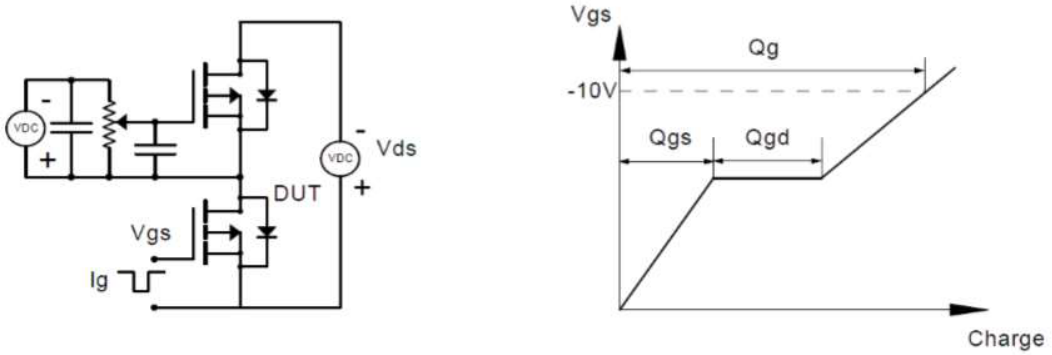


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

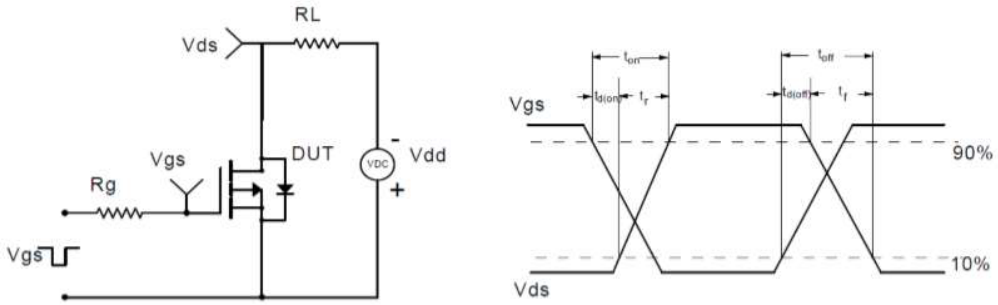


Test Circuit

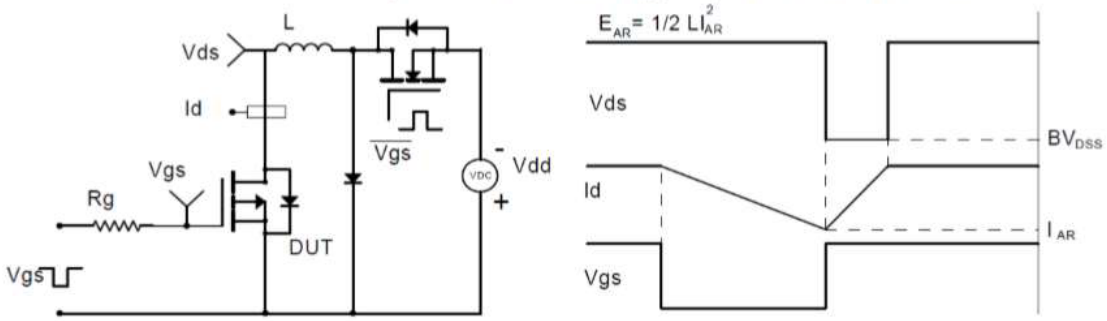
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms